Application No.:
Amendment Dated:
Reply to Office Action of:

09/990,474 April 30, 2004 January 30, 2004

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1.-4. (Canceled).
- 5. (Previously Presented) The method for forming a semiconductor device according to claim 16, in which said step f1) comprises:

depositing said second insulating film using a TEOS-CVD method utilizing TEOS activated by O_3 .

- 6.-10. (Canceled).
- 11. (Currently Amended) The method for forming a semiconductor device according to claim 16, wherein said upper <u>metal</u> layer is an Al layer.
- 12. (Previously Presented) The method for forming a semiconductor device according to claim 11, wherein

said step of depositing said Al layer comprises sputtering while heating said circuit board in a temperature range of 100 to 400°C.

- 13. (Canceled).
- 14. (Previously Presented) The method for forming a semiconductor device according to claim 16, wherein

said step of forming said surface protective film comprises depositing SiN through a plasma-excitation CVD method having an RF power of 300 W or less.

- 15. (Canceled).
- 16. (Currently Amended) A method for forming a semiconductor device,

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the method comprising the steps of:

- a) providing a circuit board;
- b) forming a first insulating film at least indirectly on said circuit board;
- c) forming a lower electrode on said first insulating film;
- d) forming a ferroelectric film over said lower electrode;
- e) forming an upper electrode over said ferroelectric film, said lower electrode, ferroelectric film, and said upper electrode combining to form a ferroelectric capacitor;
 - f) creating a synthetic tensile stress upon said ferroelectric capacitor by:
 - f1) forming a second insulating film over said ferroelectric capacitor;
 - f2) forming a metal wiring film over said second insulating film; and
- f3) forming a surface protective film over said second insulating film and said metal wiring film;

in which step f2) comprises forming the metal wiring film by:

- f2a) depositing a TiN layer as a lower metal layer;
- f2b) heat-treating said TiN layer to create a tensile stress; and
- f2c) depositing an upper metal layer directly on said TiN layer over said ferroelectric capacitor after step f2b.
- 17. (Previously Presented) The method as in claim 16, in which step f2b) comprises heat-treating said TiN layer in a temperature range of 200 to 650°C.
- 18. (Previously Presented) The method as in claim 17, in which in step f2b) said stress in said TiN layer changes from a compression-directional stress to an extensional directional stress.

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- 19. (Previously Presented) The method as in claim 16, in which in step f2b) said stress in said TiN layer changes from a compression-directional stress to an extensional directional stress.
 - 20. (Currently Amended) The method of claim 16, in which:

step f1) comprises depositing said second insulating film using a TEOS-CVD method utilizing TEOS activated by O_3 ;

step f2b) comprises heat-treating said TiN layer in a temperature range of 200 to 650°C;

said upper_metal layer is an Al layer, and said step of depositing said Al layer comprises sputtering while heating said circuit board in a temperature range of 100 to 400°C; and

said step of forming said surface protective film comprises depositing SiN through a plasma-excitation CVD method having an RF power of 300 W or less.

21. (Previously Presented) The method as in claim 20, in which in step f2b) said stress in said TiN layer changes from a compression-directional stress to an extensional directional stress.